

Name _____ Index No. _____ / _____

1920/103

BASIC ELECTRONICS

November 2015

Time: 3 hours

Candidate's Signature _____

Date _____

**THE KENYA NATIONAL EXAMINATIONS COUNCIL****CRAFT CERTIFICATE IN INFORMATION STUDIES****BASIC ELECTRONICS****3 hours****INSTRUCTIONS TO CANDIDATES***Write your **name** and **index number** in the spaces provided above.**Sign and write the date of examination in the spaces provided above.**Answer **All** questions in section **A** and any **FOUR** in section **B**.**Candidates should answer the questions in English.***For Examiner's Use Only**

| Section | Question | Maximum score | Candidate's score |
|--------------------|---------------|---------------|-------------------|
| A | 1 - 10 | 40 | |
| | 11 | 15 | |
| B | 12 | 15 | |
| | 13 | 15 | |
| | 14 | 15 | |
| | 15 | 15 | |
| Total score | | | |

This paper consists of 12 printed pages.**Candidates should check the question paper to ascertain that all the pages are printed as indicated and that no questions are missing.**

SECTION A (40 marks)

Answer **ALL** the questions in this section in the spaces provided.

1. Outline **four** sources of energy that could be used in the society. (4 marks)

2. With the aid of a sketch, outline variable capacitor symbols. (4 marks)

3. Explain **two** disadvantages of *BCD* in comparison to *binary number system*. (4 marks)

4. Determine the hexadecimal equivalent for each of the following number systems:

- (i) 572_8 ; (2 marks)

- (ii) 10001111_2 . (2 marks)

5. Calculate each of the following octal arithmetic:

(i) $453 + 444$; (2 marks)

(ii) $765 - 301$. (2 marks)

6. A conductor wire of length 24 m has a resistivity of $8 \times 10^{-4} \Omega \text{ m}$ and cross sectional area of $1.6 \times 10^{-2} \text{ m}^2$. Determine the:

(i) resistance of the wire in Ω ; (2 marks)

(ii) conductivity of the wire. (2 marks)

7. Explain **two** standard sign values for packed BCD used in computers. (4 marks)

8. Using one's complement, determine $1111\ 1001_2 - 1110\ 1000_2$.

9. Bipolar transistors have distinct regions of operation. Outline **four** of these regions defined by junction biases. (4 marks)

10. Draw a truth table for an exclusive OR (XOR) gate. (4 marks)

SECTION B (60 marks)

Answer any **FOUR** questions in this section in the spaces provided.

11. (a) (i) Explain **two** disadvantages of *flash memory* as used in computers. (4 marks)

- (ii) Differentiate between *asynchronous* and *synchronous* as a character of Static RAM. (4 marks)

- (b) (i) Determine the BCD equivalent of $1100\ 1111\ 1010\ 1001_2$. (3 marks)

- (ii) A potential difference of 10 V is connected to a uniform resistance wire of length 0.4 m and cross sectional area of $16 \times 10^{-8} \text{ m}^2$ with resistivity of $3.2 \times 10^{-6} \Omega \text{ m}$. Determine of the current flowing through the wire. (4 marks)

- (ii) Figure 1 shows an arrangement of logical gates. Construct a truth table showing the outputs R, S and T. (5 marks)

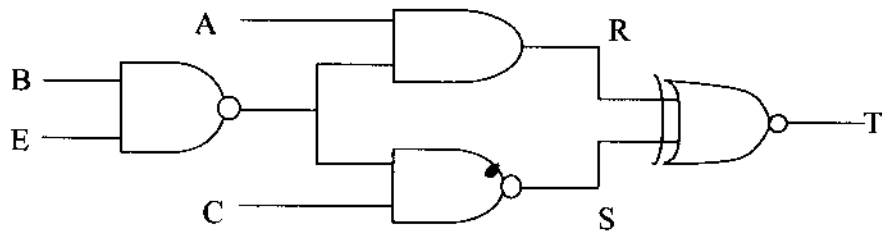


Figure 1

13. (a) (i) With the aid of sketches, outline **four** waveform shapes used in signals. (4 marks)

(ii) A current of 80 A is connected to a voltage of 16 V. Determine the:

I. resistor R (Ω) (2 marks)

II. power in R in W (microwatts) (3 marks)

(b) Simplify each of the following binary arithmetic operations giving your answer in decimal equivalent:

(i) $1001\ 0000 + 0100\ 1101$; (3 marks)

(ii) $1111\ 0100 - 1100\ 0001$. (3 marks)

14. (a) (i) State **four** applications of *diode* in the society, other than in logic gates.(2 marks)

(ii) Differentiate between *N-type* and *P-type* semiconductor materials. (4 marks)

(b) (i) Using laws of Boolean algebra, evaluate.

$$\overline{A}BC + A\overline{B}C + AB\overline{C} + ABC \quad (5 \text{ marks})$$

- (ii) Figure 2 shows a simple electric circuit with four resistors of resistance R_1 ($8\ \Omega$), R_2 ($6\ \Omega$), R_3 ($4\ \Omega$), and R_4 ($8\ \Omega$) and voltage of $80\ \text{V}$. Determine the supply current I_1 . (4 marks)

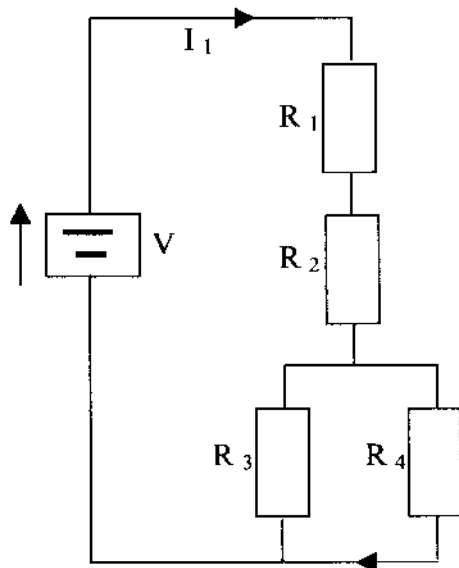


Figure 2

15. (a) (i) Outline **three** uses of extrinsic semiconductors. (3 marks)
